

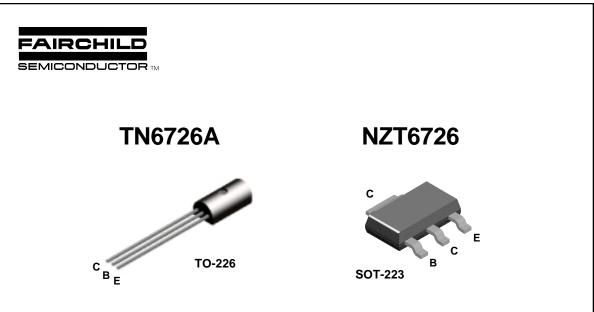
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PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0 A. Sourced from Process 77.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V _{CEO} | Collector-Emitter Voltage | 30 | V |
| V _{CBO} | Collector-Base Voltage | 40 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current - Continuous | 1.5 | А |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | | Units |
|-----------------|---|---------|----------|-------|
| | | TN6726A | *NZT6726 | |
| P _D | Total Device Dissipation | 1.0 | 1.0 | W |
| | Derate above 25°C | 8.0 | 8.0 | mW/∘C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 50 | | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 125 | 125 | °C/W |

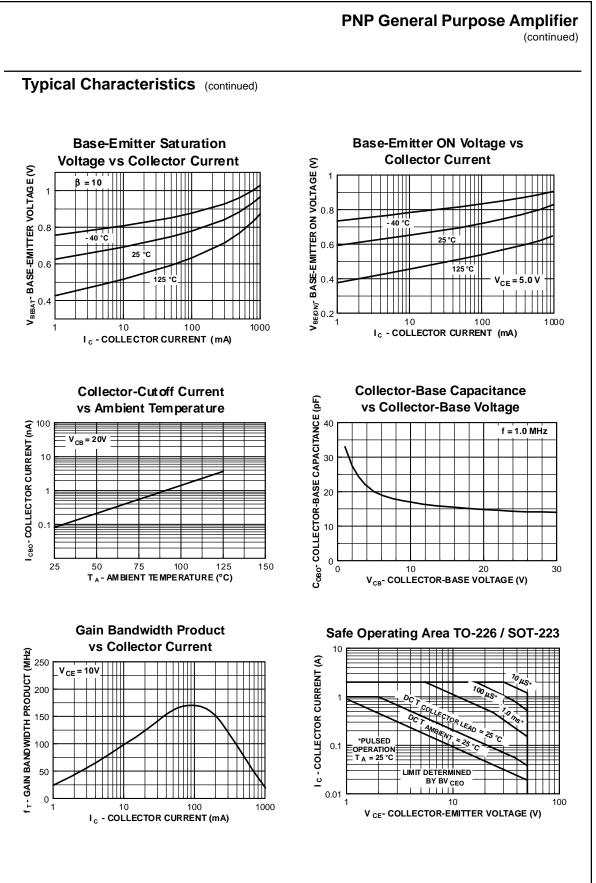
*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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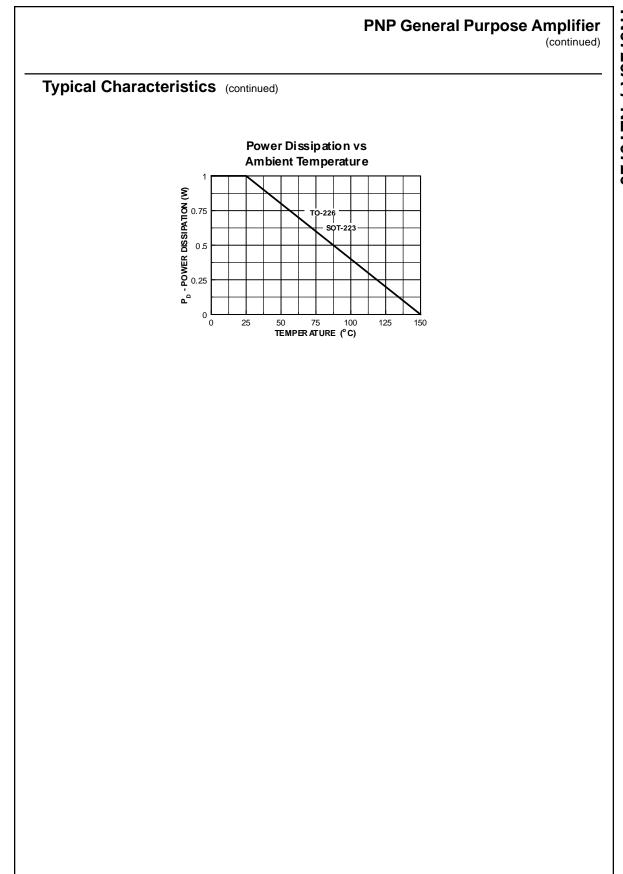
PNP General Purpose Amplifier (continued)

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|---|---|--|-----------|---------------------------------|-------|
| | RACTERISTICS | | | | |
| | Collector-Emitter Breakdown | $I_{\rm C} = 10$ mA, $I_{\rm B} = 0$ | 30 | Τ | V |
| V _{(BR)CBO} | Voltage Collector-Base Breakdown Voltage | $I_{\rm C} = 1.0 \text{ mA}, I_{\rm E} = 0$ | 40 | - | V |
| (BR)EBO | Emitter-Base Breakdown Voltage | $I_E = 100 \ \mu\text{A}, I_C = 0$ | 5.0 | - | V |
| CBO | Collector-Cutoff Current | $V_{CB} = 40 \text{ V}, \text{ I}_{E} = 0$ | 0.0 | 0.1 | μA |
| BO | Emitter-Cutoff Current | $V_{EB} = 5.0 \text{ V}, I_C = 0$ | - | 0.1 | μΑ |
| | | | <u>.</u> | | |
| N CHAR | ACTERISTICS* | | | | |
| FE | DC Current Gain | $I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ | 55 | | |
| | | $I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$ | 60 50 | 250 | |
| CE(sat) | Collector-Emitter Saturation Voltage | $I_{C} = 1.0 \text{ A}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 1.0 \text{ A}, I_{B} = 100 \text{ mA}$ | 50 | 0.5 | V |
| BE(on) | Base-Emitter On Voltage | I _C = 1.0 A, V _{CE} = 1.0 V | | 1.2 | V |
| | | | <u>,</u> | <u>,</u> | |
| MALL SI | GNAL CHARACTERISTICS | | | | |
| lfe | Small-Signal Current Gain | $I_{c} = 50 \text{ mA}, V_{CE} = 10 \text{ V},$ | 2.5 | 25 | |
| | | f = 20 MHz | | | |
| *Pulse Test: P | Collector-Base Capacitance ulse Width \leq 300 μ s, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP to | $V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz}$ ransistors. | | 30 | pF |
| *Pulse Test: P NOTE: All volta | ulse Width \leq 300 μ s, Duty Cycle \leq 1.0% | | | 30 | pF |
| *Pulse Test: P NOTE: All volta | ulse Width ≤ 300 μs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr | ransistors. Collector-E | Emitter S | | |
| *Pulse Test: P NOTE: All volta Typica | ulse Width \leq 300 μ s, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr Al Characteristics | ransistors. Collector-E | | aturation | 1 |
| NOTE: All volta | ulse Width ≤ 300 µs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current | ransistors. Collector-E | | aturation | 1 |
| *Pulse Test: P NOTE: All volta Typica | ulse Width ≤ 300 µs, Duty Cycle ≤ 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain | ransistors. Collector-E | | aturation | 1 |
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| *Pulse Test: P NOTE: All volta Typica | ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP to al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0^{\circ}$ | ransistors. Collector-E | | aturation r Current | 1 |
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| | ulse Width \leq 300 µs, Duty Cycle \leq 1.0% ages (V) and currents (A) are negative polarity for PNP tr al Characteristics Typical Pulsed Current Gain vs Collector Current $V_{CE} = 5.0V$ | ransistors. Collector-E Voltage vs $1 \qquad \beta = 10$ $0.6 \qquad \beta = 10$ $0.6 \qquad 0.4$ $0.6 \qquad 0.4$ | | aturation r Current 40 °C | |

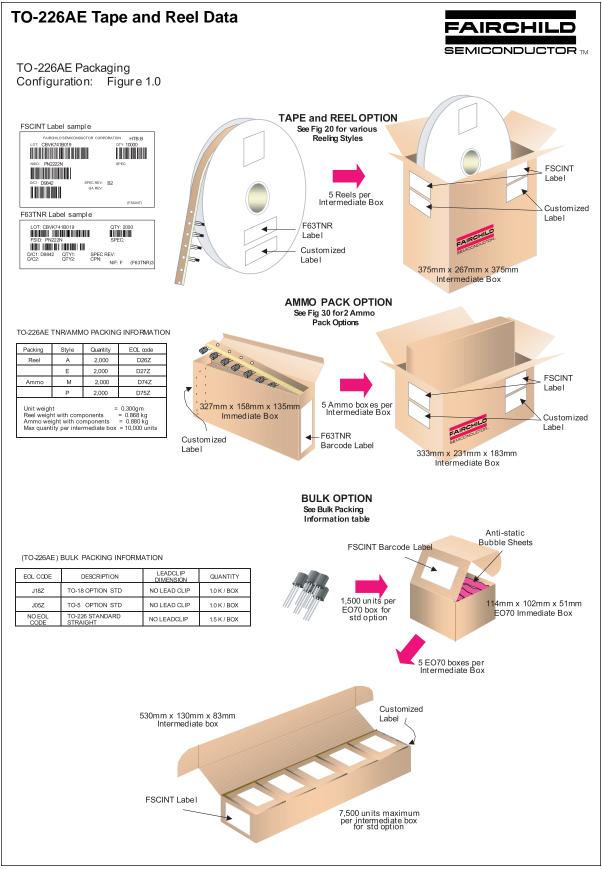
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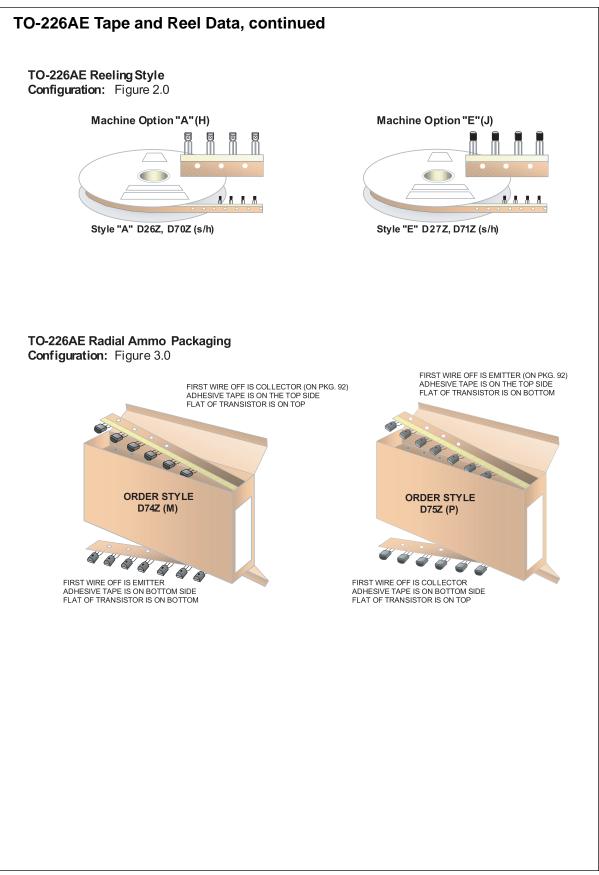


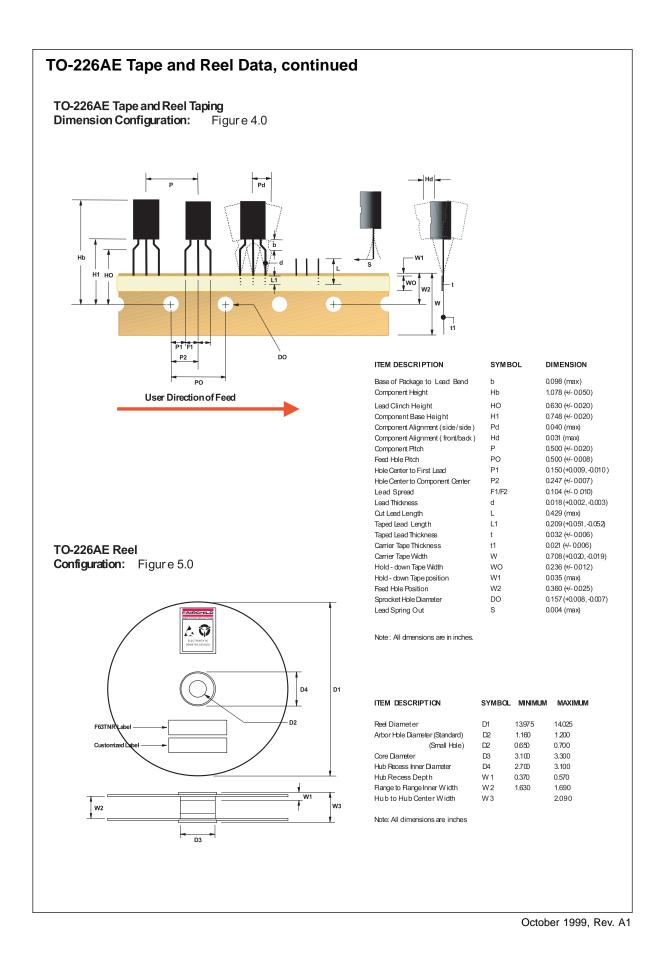
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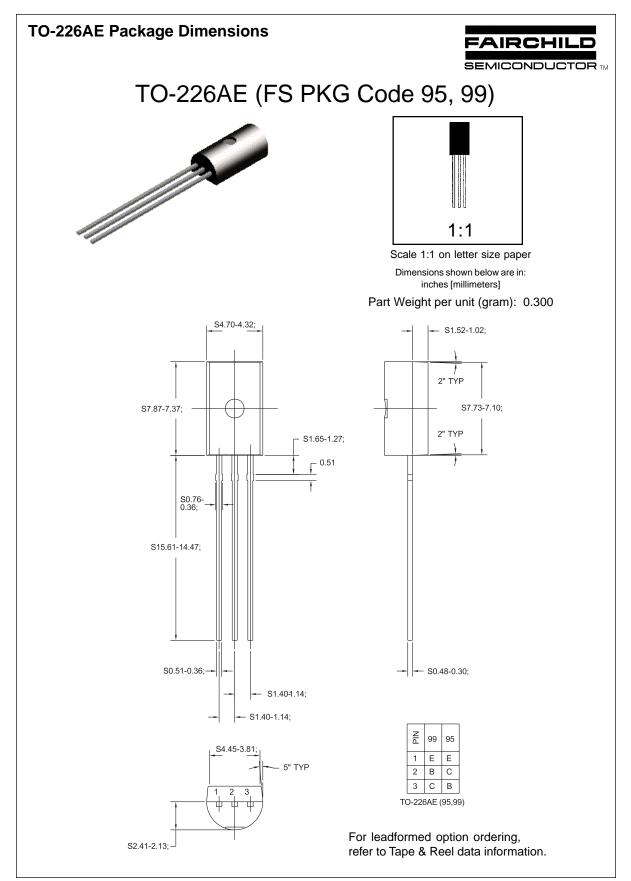


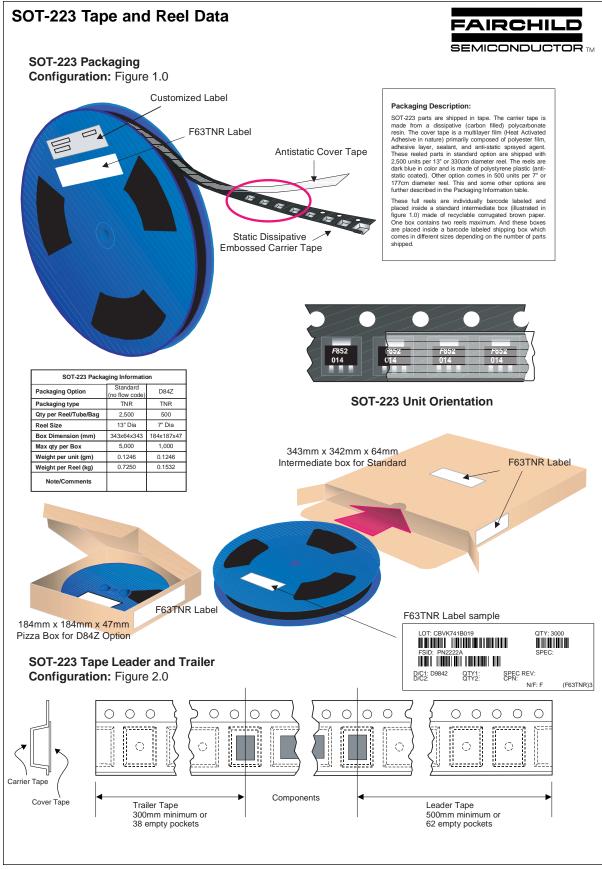
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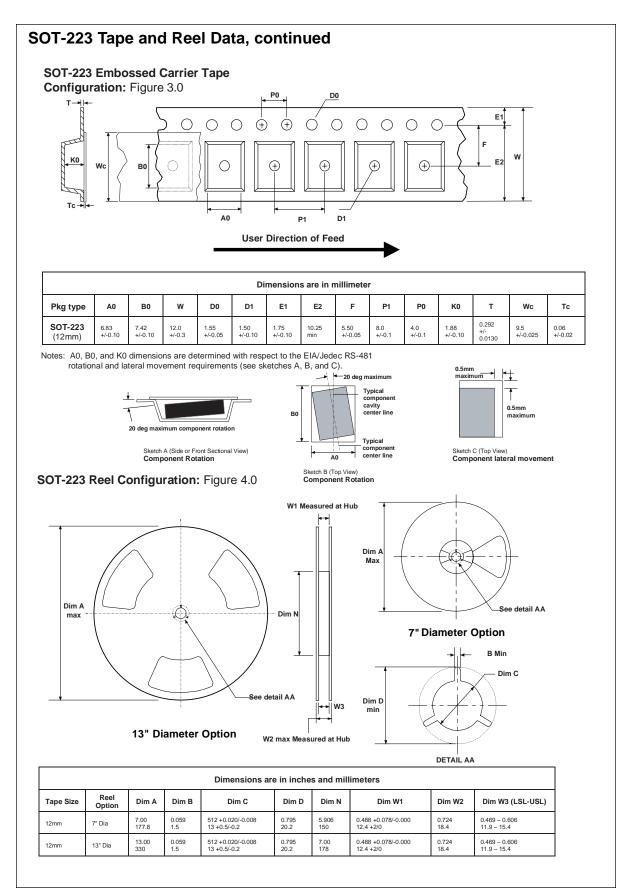


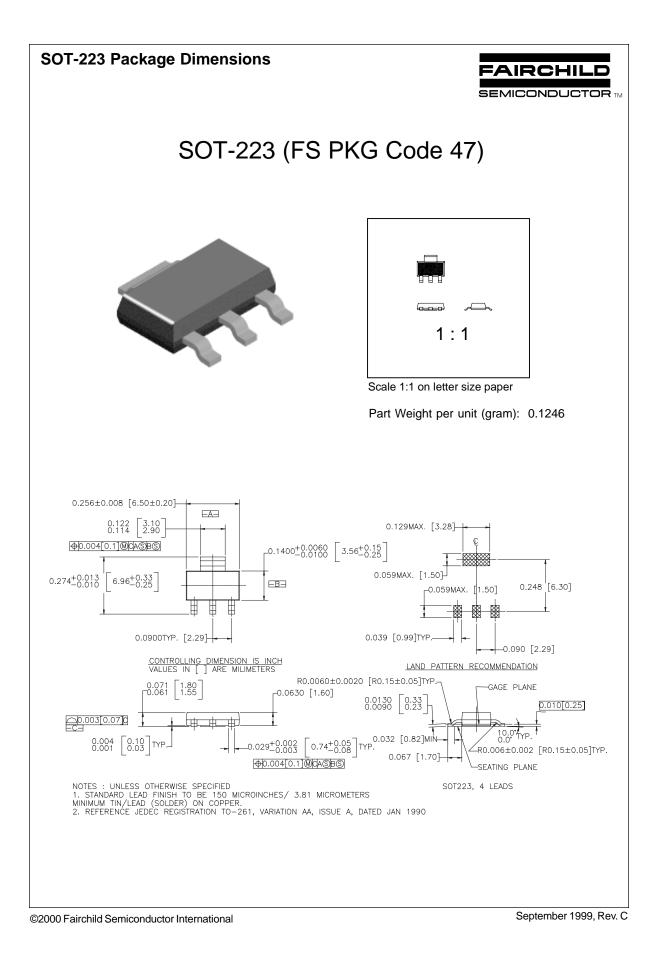




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